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12 V, single P-channel Trench MOSFET 22 November 2012

Product data sheet

1. Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 1.5 kV ESD protection (human body model)
- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- Hard disk and computing power management

1.4 Quick reference data

| Table 1. Qui | ck reference data | | | | | | |
|-------------------|----------------------------------|--|-----|-----|-----|-------|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | - | -12 | V |
| V _{GS} | gate-source voltage | - | | -12 | - | 12 | V |
| I _D | drain current | V_{GS} = -4.5 V; T_{amb} = 25 °C; t ≤ 5 s | [1] | - | - | -11.8 | А |
| Static characte | eristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = -4.5 V; I _D = -8.2 A; T _j = 25 °C | | - | 15 | 19 | mΩ |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





12 V, single P-channel Trench MOSFET

2. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-------------|-----------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | D | drain | | D |
| 2 | D | drain | | |
| 3 | G | gate | | G |
| 4 | S | source | | S 017aaa257 |
| 5 | D | drain | Transparent top view | |
| 6 | D | drain | DFN2020MD-6 (SOT1220) | |
| 7 | D | drain | | |
| 8 | S | source | | |

3. Ordering information

| Table 3. Ordering inf | formation | | | | | |
|-----------------------|-------------|--|---------|--|--|--|
| Type number | Package | 'ackage | | | | |
| | Name | Description | Version | | | |
| PMPB15XP | DFN2020MD-6 | plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals | SOT1220 | | | |

4. Marking

| Table 4. Marking codes | |
|------------------------|--------------|
| Type number | Marking code |
| PMPB15XP | 1A |

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Мах | Unit |
|------------------|-------------------------|--|-----|-----|-----------------|-----------------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | -12 | V |
| V _{GS} | gate-source voltage | | | -12 | 12 | V |
| I _D | drain current | V_{GS} = -4.5 V; T_{amb} = 25 °C; t ≤ 5 s | [1] | - | -11.8 | А |
| | | V _{GS} = -4.5 V; T _{amb} = 25 °C | [1] | - | -8.2 | А |
| | | V _{GS} = -4.5 V; T _{amb} = 100 °C | [1] | - | -5.2 | А |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$ | | - | -33 | А |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [1] | - | 1.7 | W |
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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|----------------------|-----------------------------------|-----|-----|------|------|
| | | T _{amb} = 25 °C; t ≤ 5 s | [1] | - | 3.5 | W |
| | | T _{sp} = 25 °C | | - | 12.5 | W |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drai | in diode | | 1 | | | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | -1.9 | А |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

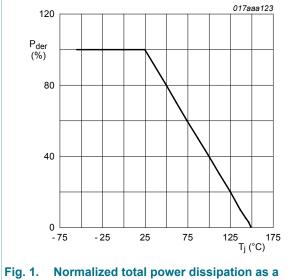


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

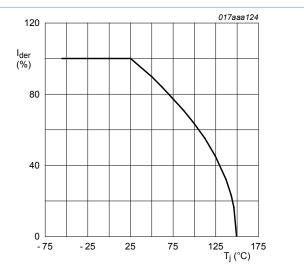
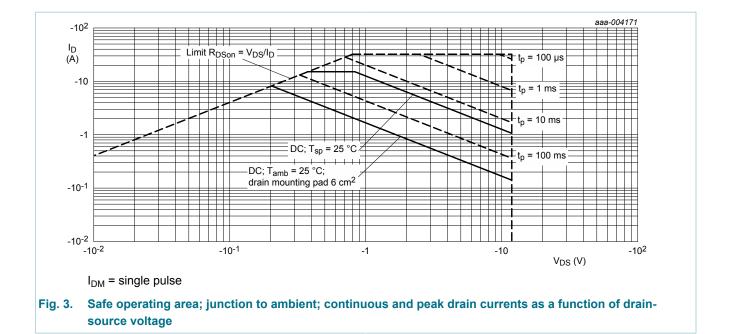


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100 \%$$

12 V, single P-channel Trench MOSFET



6. Thermal characteristics

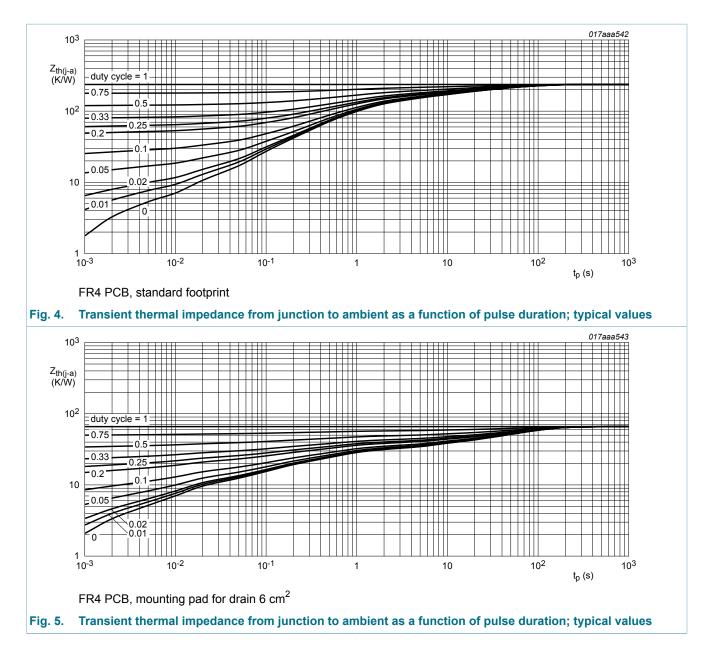
| Table 6. | Thermal characteristics | | | | | | |
|--|--|----------------------|-----|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| R _{th(j-a)} thermal resistance from junction to ambient | | in free air | [1] | - | 235 | 270 | K/W |
| | • | | [2] | - | 67 | 74 | K/W |
| | amplent | in free air; t ≤ 5 s | [2] | - | 33 | 36 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 5 | 10 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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7. Characteristics

| Table 7. Cl | haracteristics | | | | | | |
|------------------------|-----------------------------------|--|--|-------|-------|----------------|-------------------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| Static characteristics | | | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C | | -12 | - | - | V |
| V _{GSth} | gate-source threshold voltage | I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C | | -0.47 | -0.68 | -0.9 | V |
| I _{DSS} | drain leakage current | V_{DS} = -12 V; V_{GS} = 0 V; T_j = 25 °C | | - | - | -1 | μA |
| | | V _{DS} = -12 V; V _{GS} = 0 V; T _j = 150 °C | | - | - | -100 | μA |
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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|------------------------------|--|-----|------|------|------|
| I _{GSS} | gate leakage current | V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C | - | - | -100 | nA |
| | | V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C | - | - | -100 | nA |
| R _{DSon} | drain-source on-state | V_{GS} = -4.5 V; I _D = -8.2 A; T _j = 25 °C | - | 15 | 19 | mΩ |
| | resistance | V_{GS} = -4.5 V; I _D = -8.2 A; T _j = 150 °C | - | 20 | 25 | mΩ |
| | | V_{GS} = -2.5 V; I _D = -3.9 A; T _j = 25 °C | - | 17 | 20 | mΩ |
| | | V_{GS} = -1.8 V; I _D = -3.9 A; T _j = 25 °C | - | 21 | 33 | mΩ |
| 9 _{fs} | forward transconductance | V _{DS} = -10 V; I _D = -8.2 A; T _j = 25 °C | - | 40 | - | S |
| Dynamic cl | haracteristics | · · · | I | I | | |
| Q _{G(tot)} | total gate charge | V_{DS} = -6 V; I _D = -8.2 A; V _{GS} = -4.5 V; | - | 67 | 100 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 5.5 | - | nC |
| Q _{GD} | gate-drain charge | | - | 7.3 | - | nC |
| C _{iss} | input capacitance | V_{DS} = -6 V; f = 1 MHz; V_{GS} = 0 V; | - | 2875 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 570 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 530 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = -6 V; I _D = -8.2 A; V _{GS} = -4.5 V; | - | 18 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 90 | - | ns |
| t _{d(off)} | turn-off delay time | 1 | - | 85 | - | ns |
| t _f | fall time | | - | 57 | - | ns |

Source-drain diode

source-drain voltage

 V_{SD}

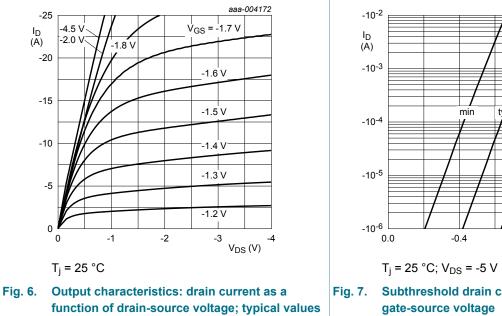
 I_{S} = -1.9 A; V_{GS} = 0 V; T_{j} = 25 °C

-1.2

aaa-004173

V

-0.6



typ max -0.8 -1.2 $V_{GS}(V)$ Fig. 7. Subthreshold drain current as a function of

_

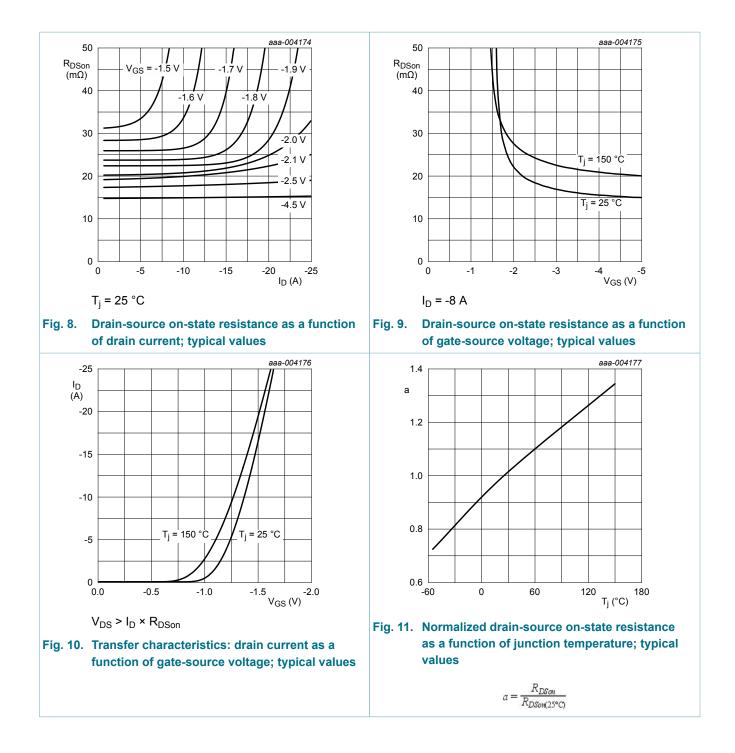


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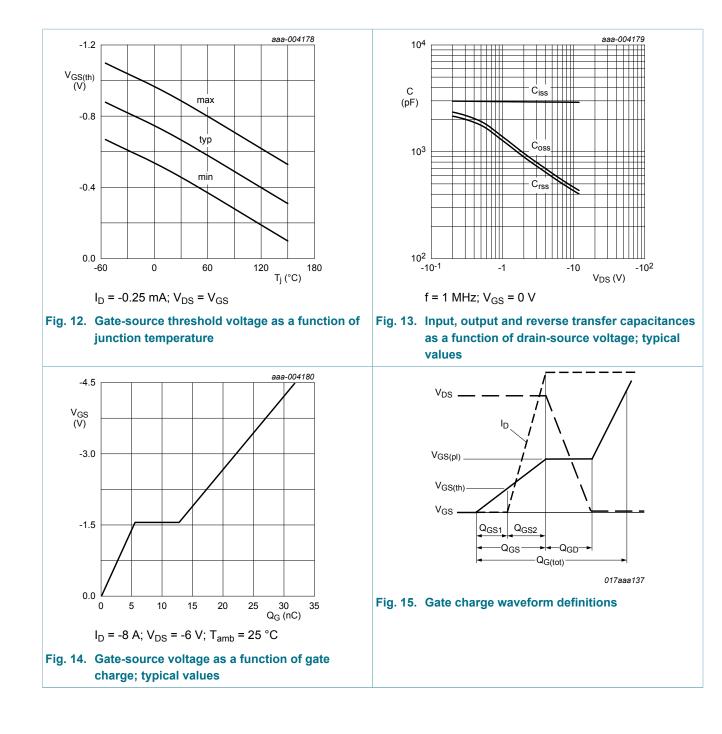
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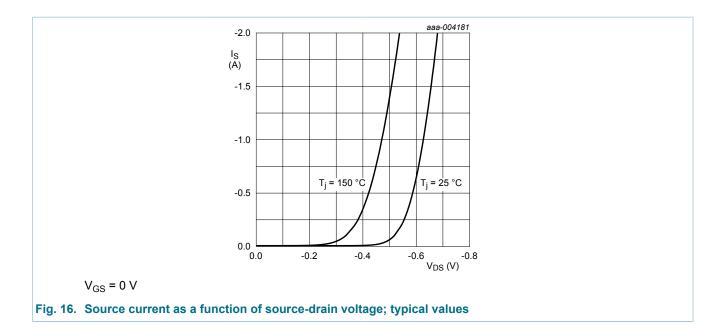
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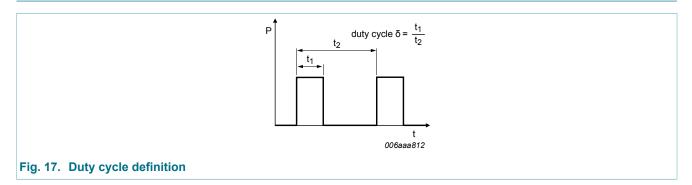


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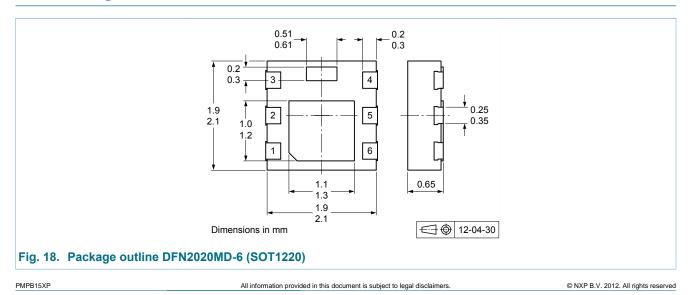
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8. Test information

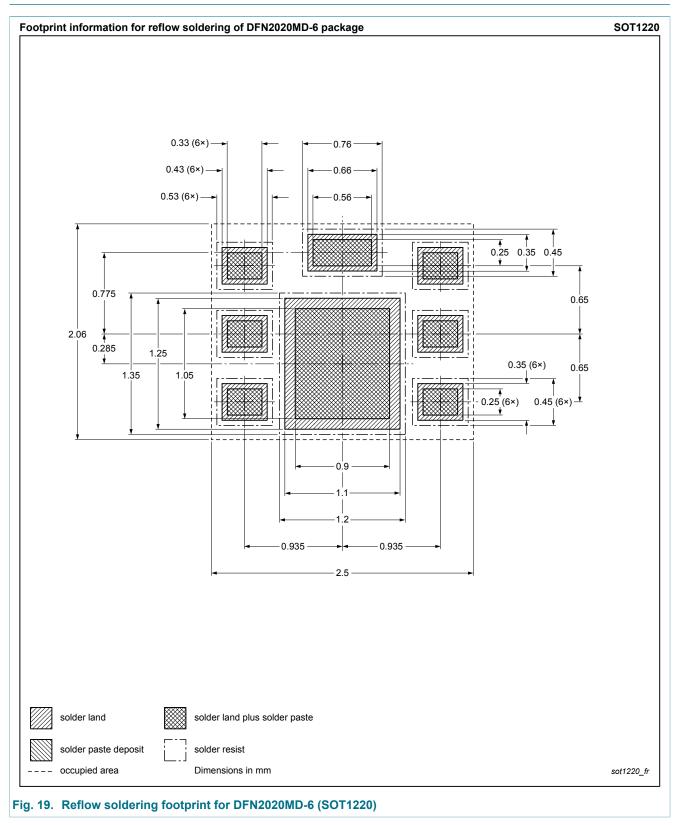


9. Package outline



12 V, single P-channel Trench MOSFET

10. Soldering



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11. Revision history

| Table 8. Revision hi | story | | | |
|----------------------|--------------------|--|----------------|--------------|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
| PMPB15XP v.3 | 20121122 | Product data sheet | - | PMPB15XP v.2 |
| Modifications: | Table 7 "Character | istics": R _{DSon} at V _{GS} = -1.8 | 8 V corrected. | |
| PMPB15XP v.2 | 20120719 | Product data sheet | - | PMPB15XP v.1 |
| PMPB15XP v.1 | 20120706 | Preliminary data sheet | - | - |

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12. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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